

Focused Ion & Electron Beam Sys

Hitachi's high performance FIB-SEM provides unparalleled nano-analyses of devices and functional materials!!

Legendary Hitachi reliability and performance in an integrated system (Ultra-high performance FIB and high resolution FE-SEM) enabling high-throughput specimen preparation, high resolution imaging and analysis and precision nanofabrication. New low-damage fabrication techniques have been developed for materials sensitive to electron irradiation. Innovations in sample loading, sample navigation, and Micro-sampling increase analysis efficiency*1.



nanoDUE'T NB5000

Features

Ultra-high performance FIB

Low Cs FIB optics*2 deliver 50nA or more of beam current (@40kV) in an about 1 μ m spot-size. The high current enables unconventional large-area milling, hard material fabrication and high throughput multiple specimen preparation.

New Micro-sampling*2

Hitachi's patented Micro-sampling technology provides smooth probe motion. Also, the probe can be used for newly developed absorbed current imaging*1 to aid fault isolation.

High precision end-point detection

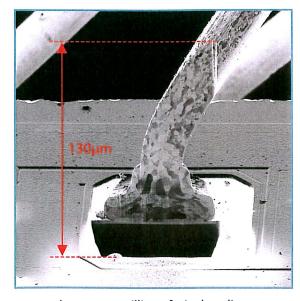
High resolution SEM allows high precision end-point detection. Section-view function, which displays an outline of the cross-section utilizing the real-time FIB image, is ideal for preparing electron irradiation sensitive specimens like Low-K material.

High resolution SEM

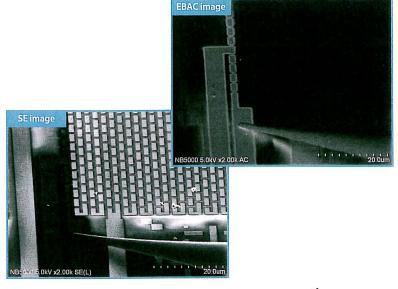
Hitachi's unparalleled SEM column and detector design*2 enables high resolution SEM imaging during and after FIB fabrication.

Holder compatibility with TEM/STEM*1,*2

A side entry STEM/TEM-type stage* 1 allows the use of the same specimen holder (compatible with NB5000 and Hitachi TEM/STEM) . No tweezer handling of specimen during transfer results in higher throughput TEM/STEM analysis.



 $Large-area\ milling\ of\ wire\ bonding \\ (milled\ area: 75\ (w)\times 130\ (h)\ \mu m,\ milling\ time: 19min.)$



EBAC (Electron Beam Absorbed Current) imaging*1 with new Micro-sampling system

^{*1} Optional accessory

^{*2} Hitachi patent Low Cs FIB optics: patent pending, Micro-sampling: JP2774884/US5270552, Section-view function: patent pending, SEM column and detector design: JP3081393,US5387793, Holder compatibility: JP2842083

Specification

2015 Inches on the con-			
Accelerating voltage	1 ~ 40kV		
Beam current	50 nA or more @40kV (CP)		
SIM resolution	5nm @ 40kV (CP)		
Magnification	×60 ∼ ×250,000		
Ion source	Ga Liquid Metal Ion Source		
Lens system	Low Cs 2-stage electrostatic lens system		
Accelerating voltage	0.5 ~ 30kV		
OCM	1.0 nm @15kV (CP)		
SEIVI resolution	2.1 nm @1kV (OWD)*2		
Magnification High Mag mode Low Mag mode	×250 ~ ×800,000		
	×70 ∼ ×2,000		
Electron source	ZrO/W Schottky emission		
Lens system	3-stage electromagnetic lens reduction system		
SEM	Upper SE, Lower SE, Absorbed current*1		
FIB	Lower SE, Absorbed current*1		
Traverse range	X : 50mm (30mm*²), Y : 50mm (30mm*²), Z : 22mm		
	T : -1.5 \sim 58.3°, R : 360°		
Maximum diameter	φ50mm (φ30mm*²)		
Material	Tungsten/Carbon (changeable)		
Probe exchange	Load lock type		
Additional function	Touch sensing, Absorbed current imaging*1		
	SIM resolution Magnification Ion source Lens system Accelerating voltage SEM resolution Magnification High Mag mode Low Mag mode Electron source Lens system SEM FIB Traverse range Maximum diameter Material Probe exchange		

CP : Beam Cross Point

OWD : Optimum Working Distance

Optional accessories

Holder scope, Absorbed current imaging, Automatic fabrication software, Side entry stage, Specimen rotation holder, Energy Dispersive X-ray spectrometer (EDX), Water circulator, Air compressor, Dry pump

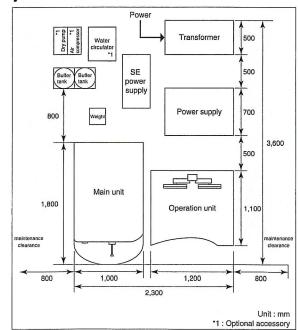
Dimensions and weight

Unit	Width × Dep	oth × He	ight (mm)	We	eight (kg)
Main unit	933 × 1	,747 ×	1,900		1,129
Operation unit	1,200 × 1	,025 ×	740		188
Power supply	980 ×	640 ×	1,565		463
Transformer	980 ×	454 ×	625		192
SE power supply	394 ×	754 ×	780		122
Buffer tank (×2)	@280 ×	280 ×	665		@18
Dry pump*1	400 ×	252 ×	336		25
Water circulator*1	450 ×	400 ×	660		55
Air compressor*1	400 ×	230 ×	550		18
Weight	200 ×	180 ×	160		40
					*1 Ontional accessor

*1 Optional accessory

Layout

*1 Optional accessory
*2 When side entry stage is ordered



Utilities

Temperature	$15^{\circ}\text{C} \sim 25^{\circ}\text{C}$ (Variation during operation : 2°C or less/hr)
Humidity	60% RH or lower
Power	Single phase 200V (±10%), 8kVA (50/60Hz)
Grounding	D class, Grounding resistance : 100Ω or less
Water	Please use a water circulator.
	Flow rate : 1.0 \sim 1.3L/min (Water pressure : 50 \sim 130kPa)
	Water temperature : 10 \sim 20 $^{\circ}$ C (Variation : 0.5 $^{\circ}$ C or less/10 min.)
Gas	Air $0.4 \sim 0.6$ MPa, For valve control
	N_2 gas 30 \sim 50kPa, Needed for N2 gas column leak

NOTICE: For proper operation, follow the instruction manual when using the instrument.

Specifications in this catalog are subject to change with or without notice, as Hitachi High-Technologies Corporation continues to develop the latest technologies and products for our customers.

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